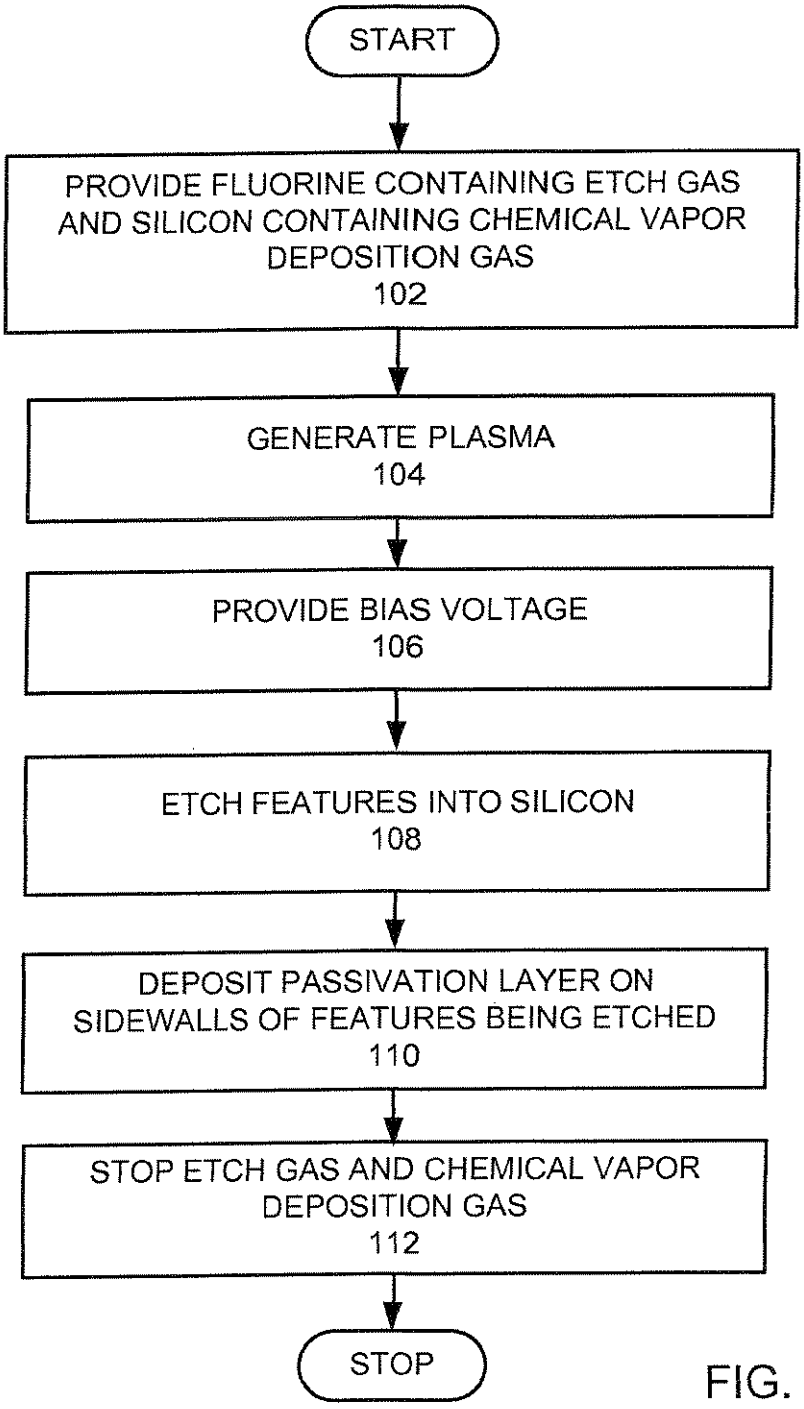

START
PROVIDE FLUORINE CONTAINING ETCH GAS AND SILICON CONTAINING CHEMICAL VAPOR DEPOSITION GAS
102
GENERATE PLASMA
104
PROVIDE BIAS VOLTAGE
106
ETCH FEATURES INTO SILICON
108
DEPOSIT PASSIVATION LAYER ON SIDEWALLS OF FEATURES BEING ETCHED
110
STOP ETCH GAS AND CHEMICAL VAPOR DEPOSITION GAS
112
STOP

FIG. 1

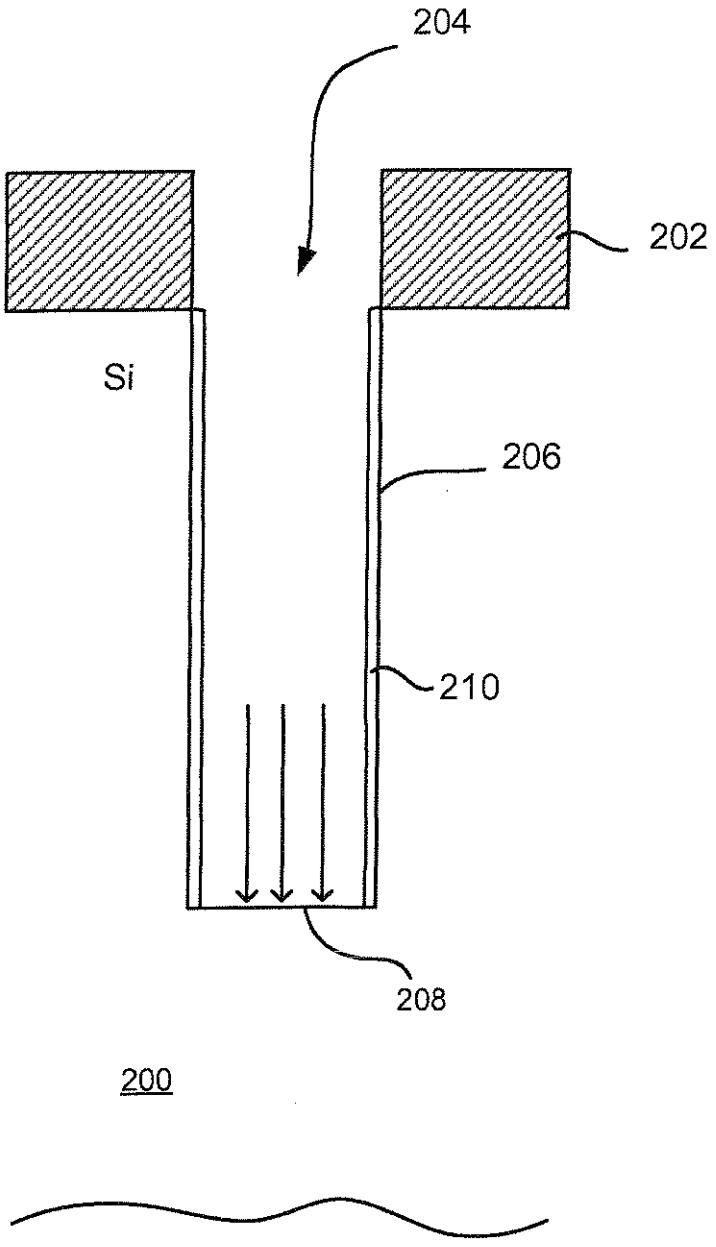


FIG. 2

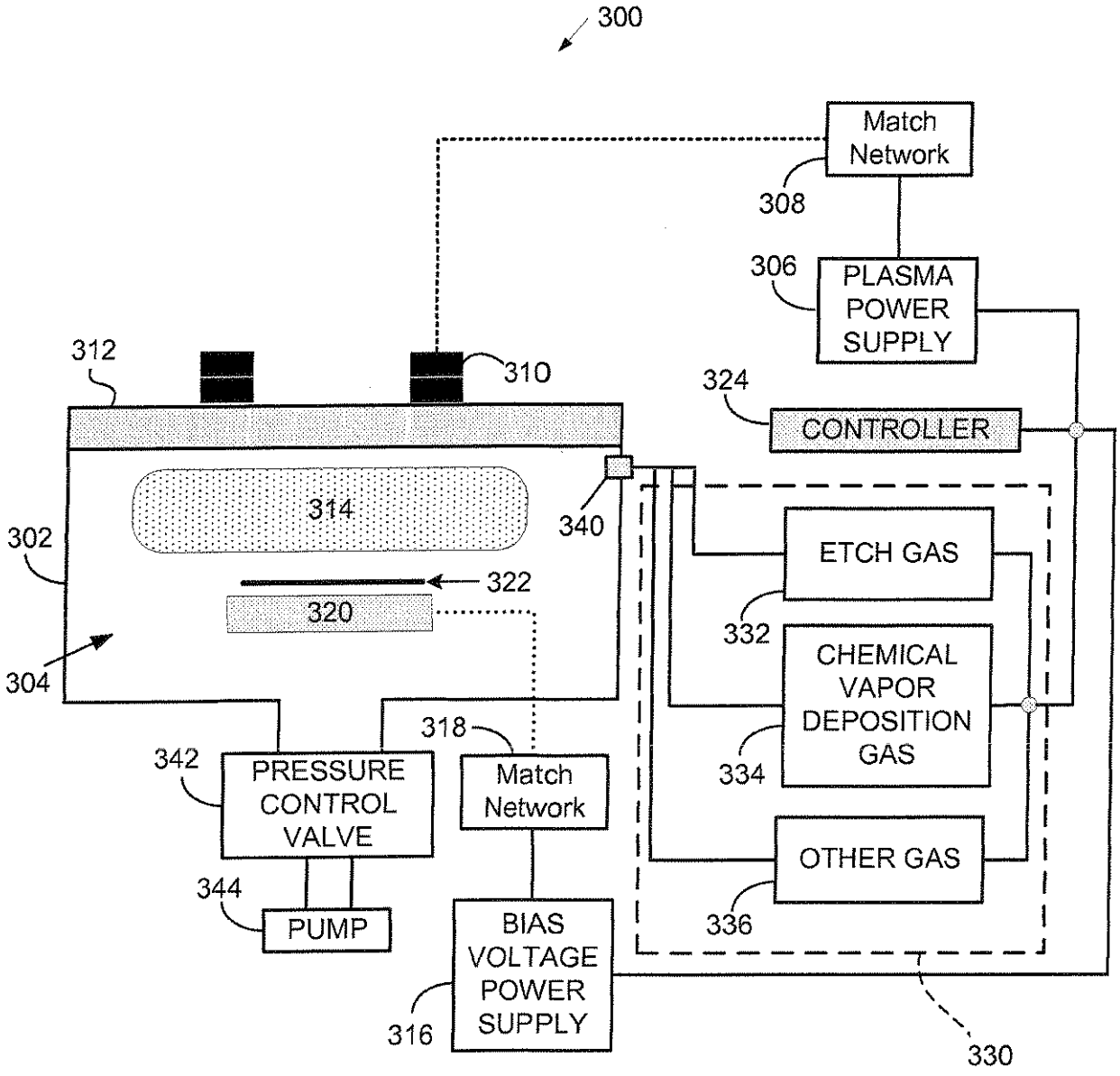

300
Match Network
308
306
PLASMA POWER SUPPLY
312
310
324
CONTROLLER
314
340
302
ETCH GAS
322
320
332
CHEMICAL VAPOR DEPOSITION GAS
304
318
342
PRESSURE CONTROL VALVE
Match Network
334
OTHER GAS
344
PUMP
336
BIAS VOLTAGE POWER SUPPLY
316
330

FIG. 3

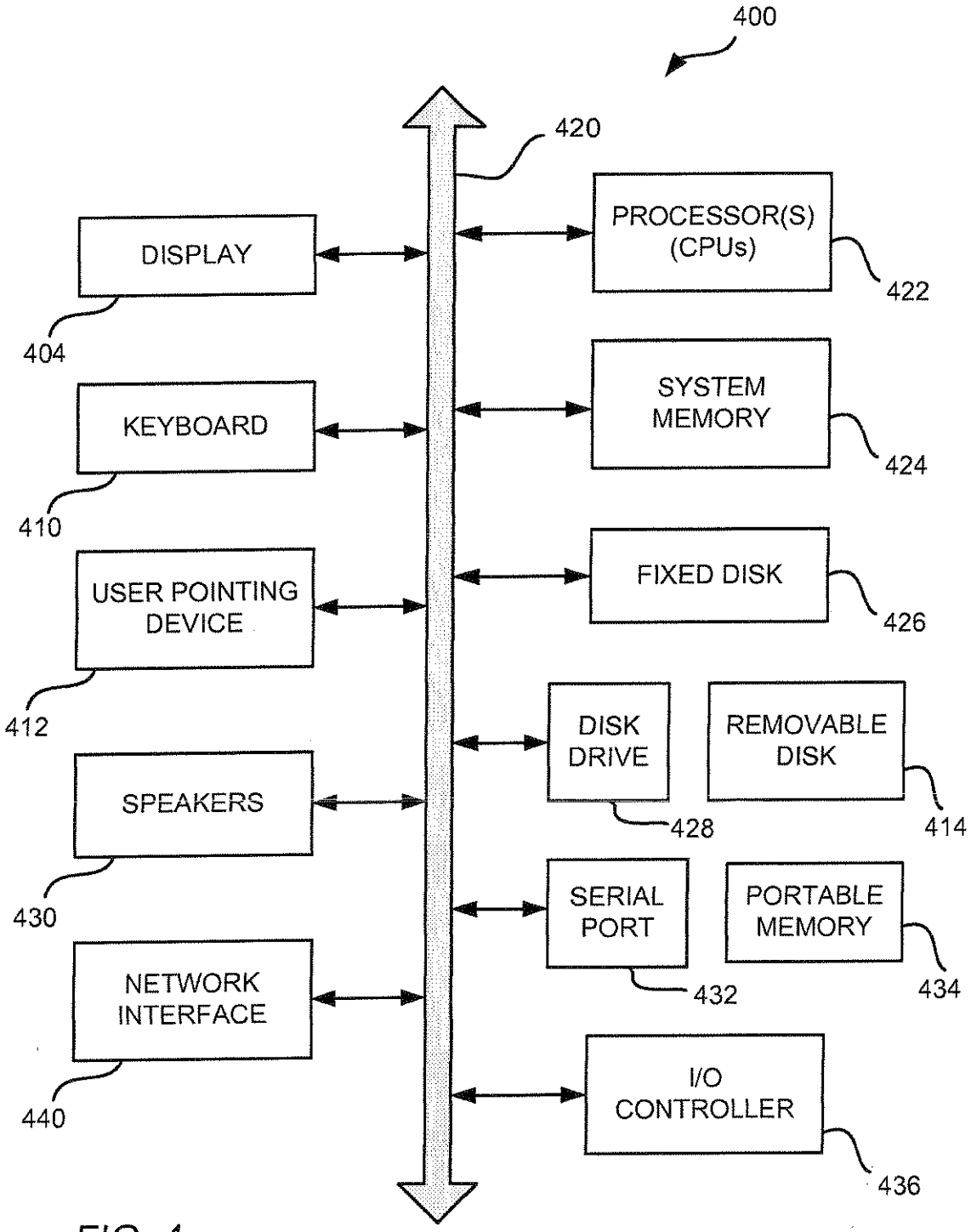

400
420
DISPLAY
404
KEYBOARD
410
USER POINTING DEVICE
412
SPEAKERS
430
NETWORK INTERFACE
440
PROCESSOR(S) (CPUs)
422
SYSTEM MEMORY
424
FIXED DISK
426
DISK DRIVE
428
REMOVABLE DISK
414
SERIAL PORT
432
PORTABLE MEMORY
434
I/O CONTROLLER
436

FIG. 4

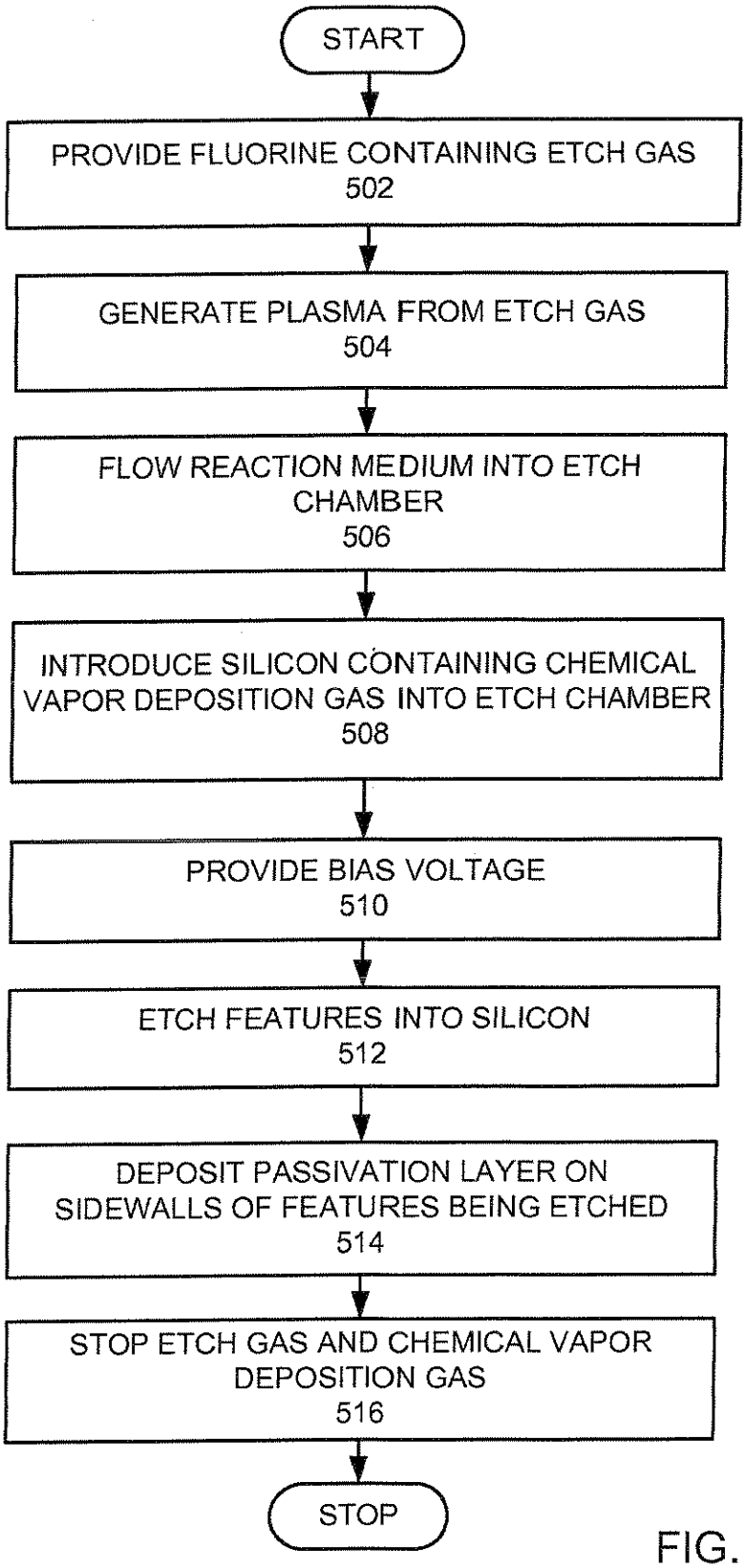

START
PROVIDE FLUORINE CONTAINING ETCH GAS
502
GENERATE PLASMA FROM ETCH GAS
504
FLOW REACTION MEDIUM INTO ETCH CHAMBER
506
INTRODUCE SILICON CONTAINING CHEMICAL VAPOR DEPOSITION GAS INTO ETCH CHAMBER
508
PROVIDE BIAS VOLTAGE
510
ETCH FEATURES INTO SILICON
512
DEPOSIT PASSIVATION LAYER ON SIDEWALLS OF FEATURES BEING ETCHED
514
STOP ETCH GAS AND CHEMICAL VAPOR DEPOSITION GAS
516
STOP

FIG. 5

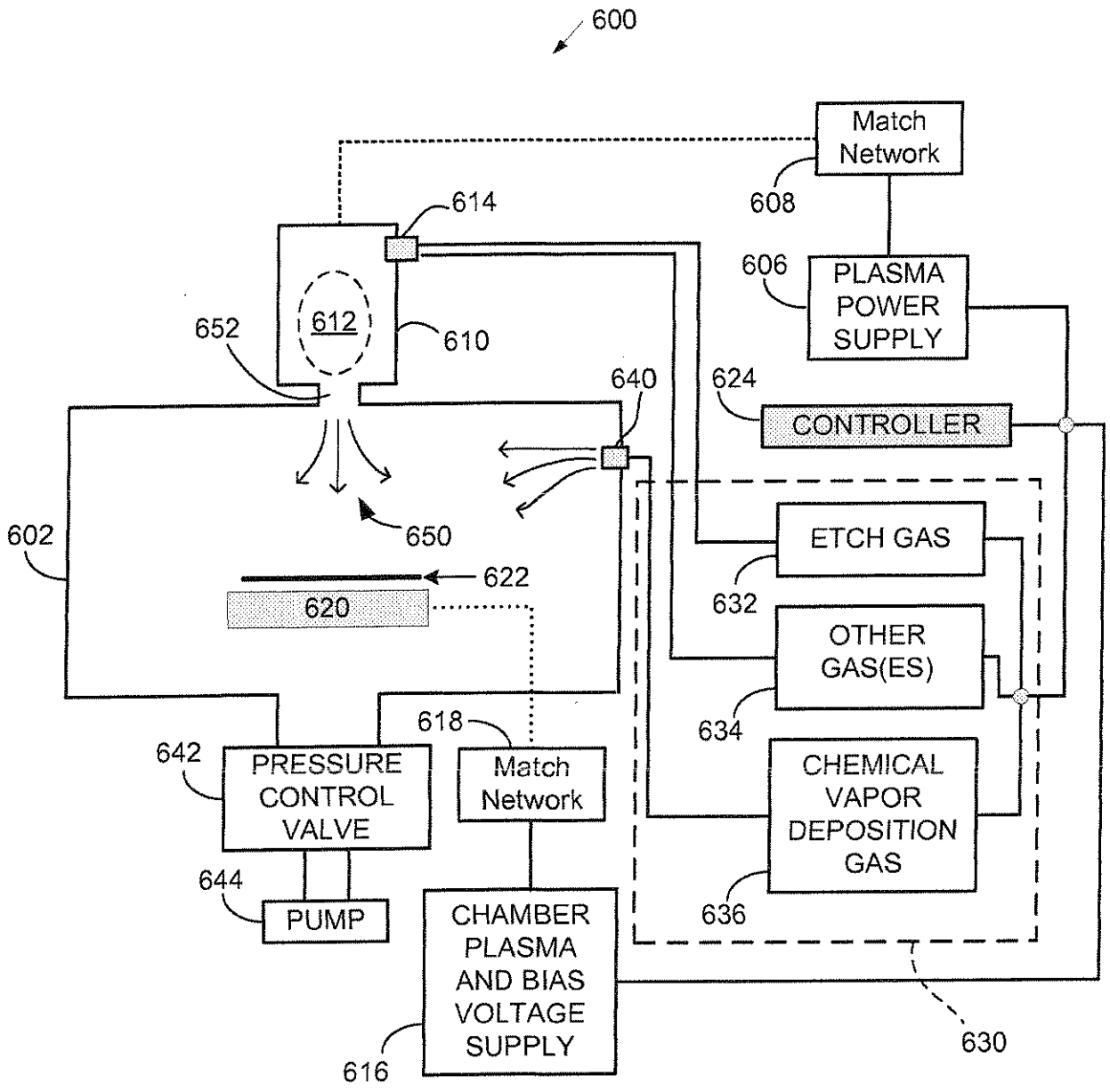

600
Match Network
608
614
606
PLASMA POWER SUPPLY
652
612
610
640
624
CONTROLLER
602
650
ETCH GAS
622
620
632
OTHER GAS(ES)
634
618
642
PRESSURE CONTROL VALVE
Match Network
CHEMICAL VAPOR DEPOSITION GAS
644
PUMP
636
CHAMBER PLASMA AND BIAS VOLTAGE SUPPLY
630
616

FIG. 6